1. Record Nr. UNINA990001152290403321

Autore	Cvijic, Jovan <1865-1927>
Titolo	La péninsule balkanique : géographie humaine / Jovan Cvijic
Pubbl/distr/stampa	Paris : A. Colin, 1918
Descrizione fisica	VIII, 528 p., [9] c. di tav. ripieg. : ill. ; 26 cm
Disciplina	061.001
Locazione	DECGE ILFGE MA1
Collocazione	061.001.CVI H-03-015 211-H-6
Lingua di pubblicazione	Francese
Formato	Materiale a stampa
Livello bibliografico	Monografia

2. Record Nr. UNINA9910961790903321

Autore	Galup-Montoro Carlos
Titolo	MOSFET modeling for circuit analysis and design / / Carlos Galup-Montoro, Marcio Cherem Schneider
Pubbl/distr/stampa	Singapore ; ; Hackensack, NJ, : World Scientific, c2007
ISBN	9786611120870 9781281120878 1281120871 9789812707598 981270759X
Edizione	[1st ed.]
Descrizione fisica	1 online resource (445 p.)
Collana	International series on advances in solid state electronics and technology
Altri autori (Persone)	SchneiderMarcio Cherem
Disciplina	621.3815284
Soggetti	Metal oxide semiconductor field-effect transistors - Mathematical models Field-effect transistors - Mathematical models
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Foreword; Preface; Contents; List of Selected Symbols; Chapter 1 Introduction; Chapter 2 The MOS Capacitor; Chapter 3 The Long-Channel MOSFET: Theory and dc Equations; Chapter 4 The Real MOS Transistor: dc Models; Chapter 5 Stored Charges and Capacitive Coefficients; Chapter 6 Mismatch Modeling; Chapter 7 Noise in MOSFETs; Chapter 8 High-Frequency Models; Chapter 9 Gate and Bulk Currents; Chapter 10 Advanced MOSFET Structures; Chapter 11 MOSFET Parameter Extraction; Chapter 12 Advanced MOSFET Models for Circuit Simulators; Appendix A Electrostatics in One Dimension Appendix B Electrostatics in SemiconductorsAppendix C Drift-diffusion Current Model; Appendix D Continuity Equations; Appendix E Basics of pn Junctions; Appendix F Hall-Shockley-Read (HSR) Statistics; Appendix G Interface Trap Capacitance; Index
Sommario/riassunto	This is the first book dedicated to the next generation of MOSFET models. Addressed to circuit designers with an in-depth treatment that appeals to device specialists, the book presents a fresh view of

compact modeling, having completely abandoned the regional modeling approach. Both an overview of the basic physics theory required to build compact MOSFET models and a unified treatment of inversion-charge and surface-potential models are provided. The needs of digital, analog and RF designers as regards the availability of simple equations for circuit designs are taken into account. Compact ex